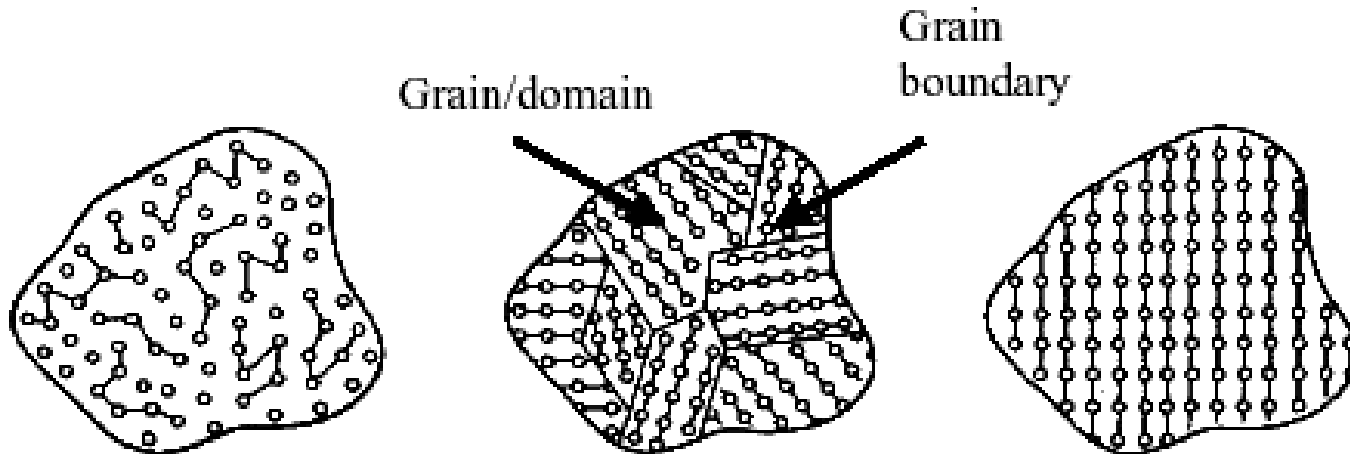
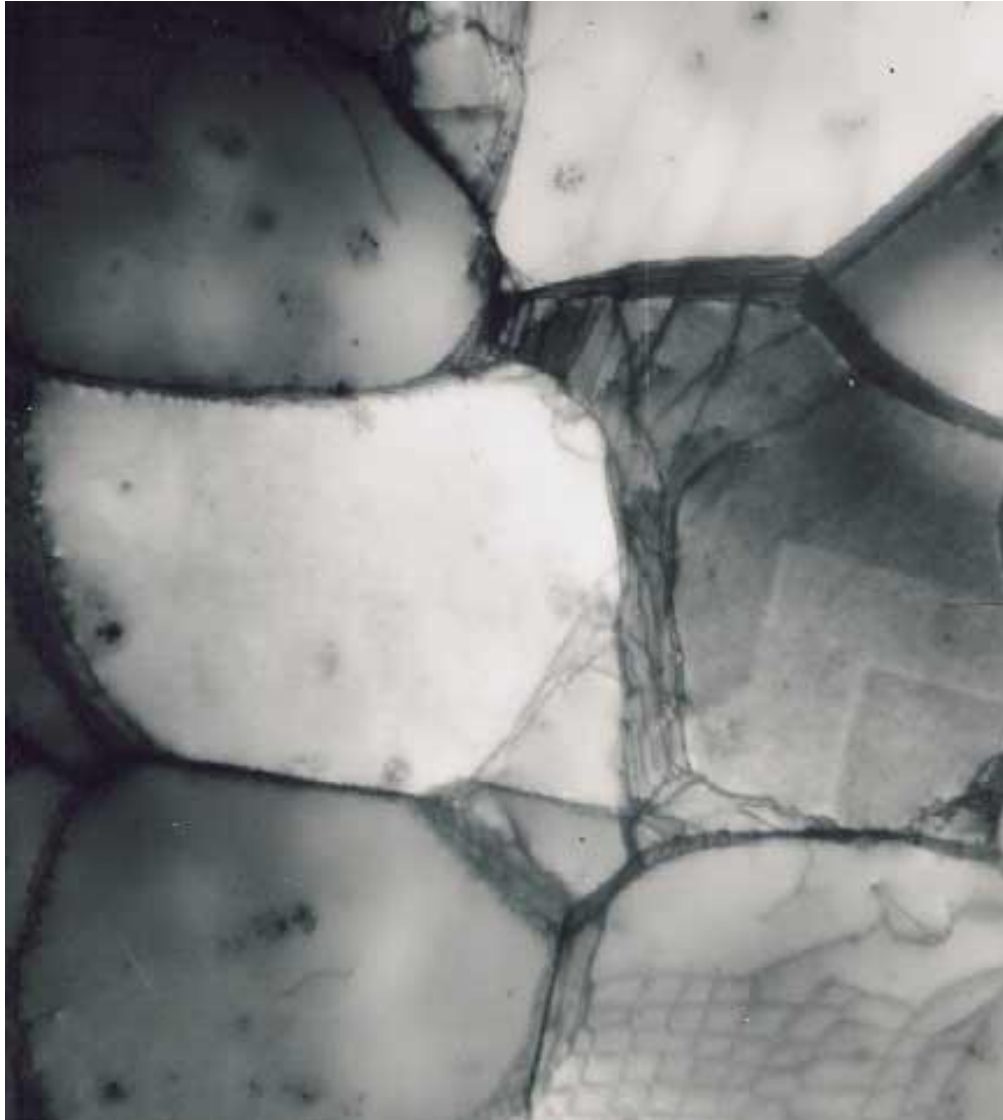


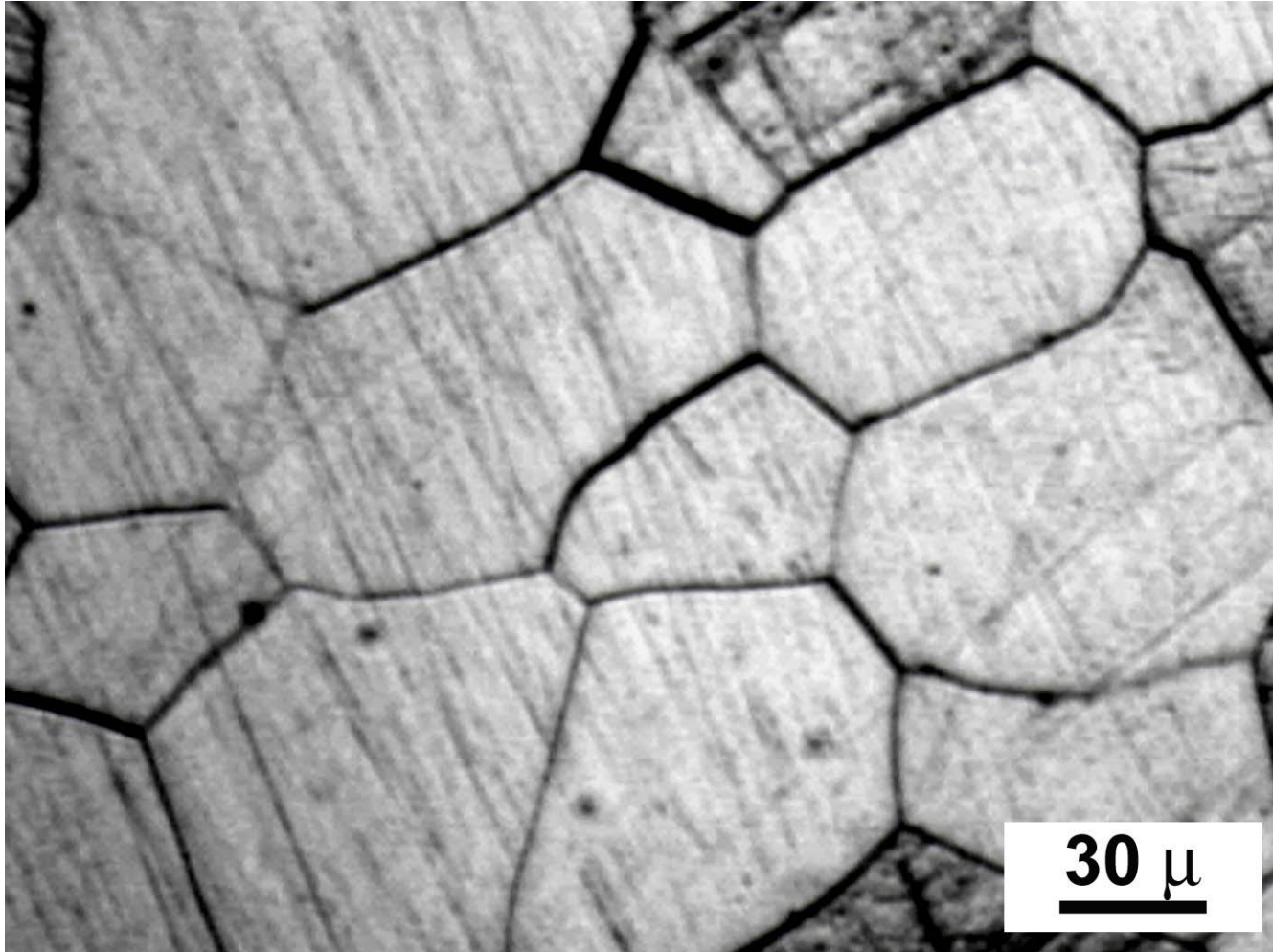
crystalline structures

materials:
amorphous – polycrystalline – monocrystalline





TEM, Al film



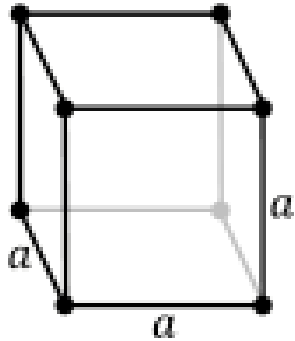
steel

acid etched
surface



natural
diamonds

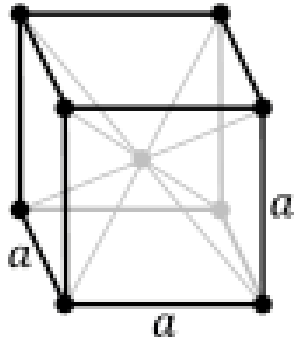
crystal lattices:



Simple Cubic lattice

Po

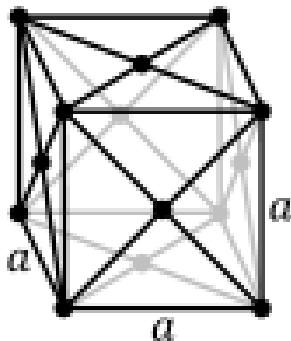
52 % filling



Body Centered Cubic lattice, BCC

α -Fe, Li, Na, K, Na, Mo, Cr, W

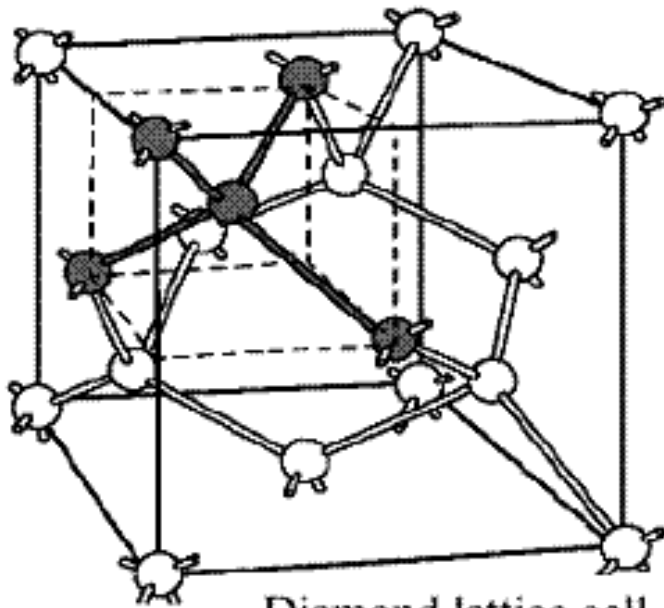
68 % filling



Face Centered Cubic lattice, FCC

Cu, Ag, Au, Al, Ca, Ni, Pb, Pt, Pd, α -Fe

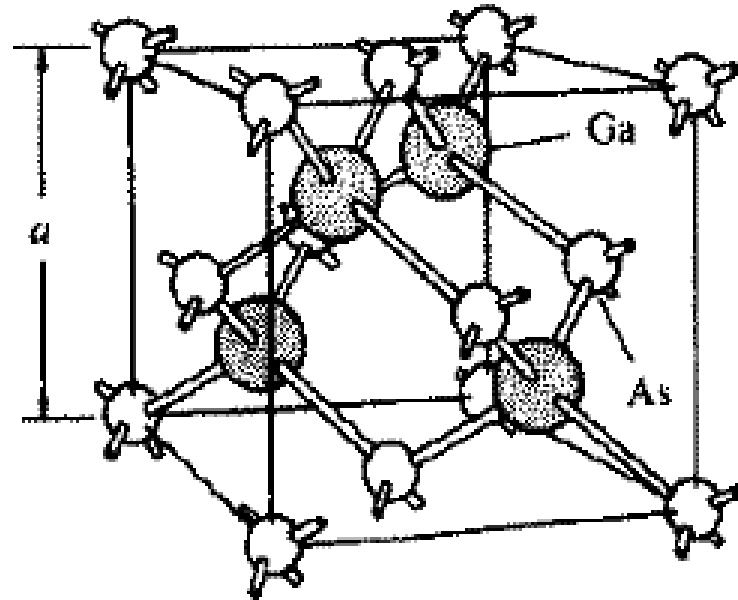
74 % filling



Diamond lattice cell

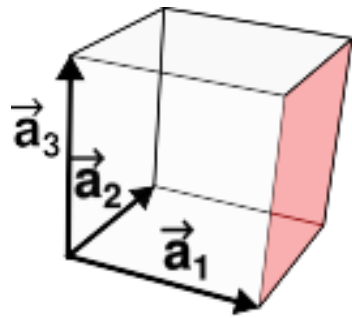
diamond lattice
(C, Si, Ge, Sn)

34 % filling

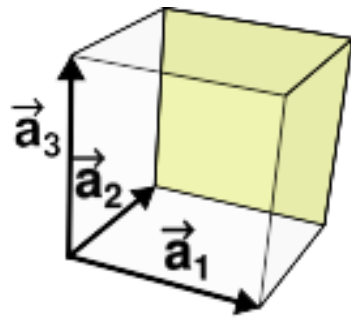


Zincblende lattice cell

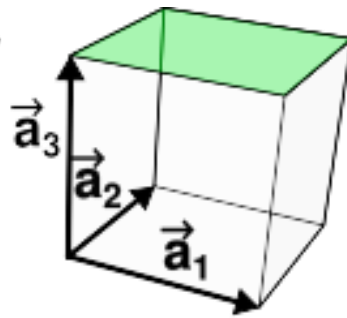
zincblende lattice
(ZnS, GaAs, CdTe, InP, ZnSe)



(100)

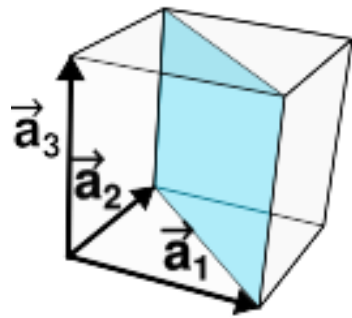


(010)

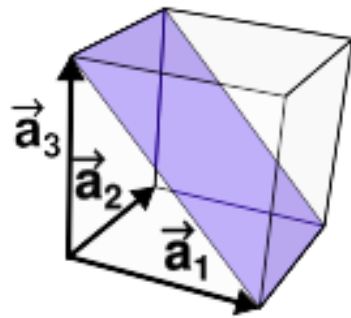


(001)

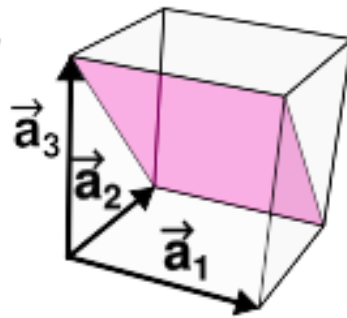
Miller indices (hkl)
describe crystal planes



(110)



(101)

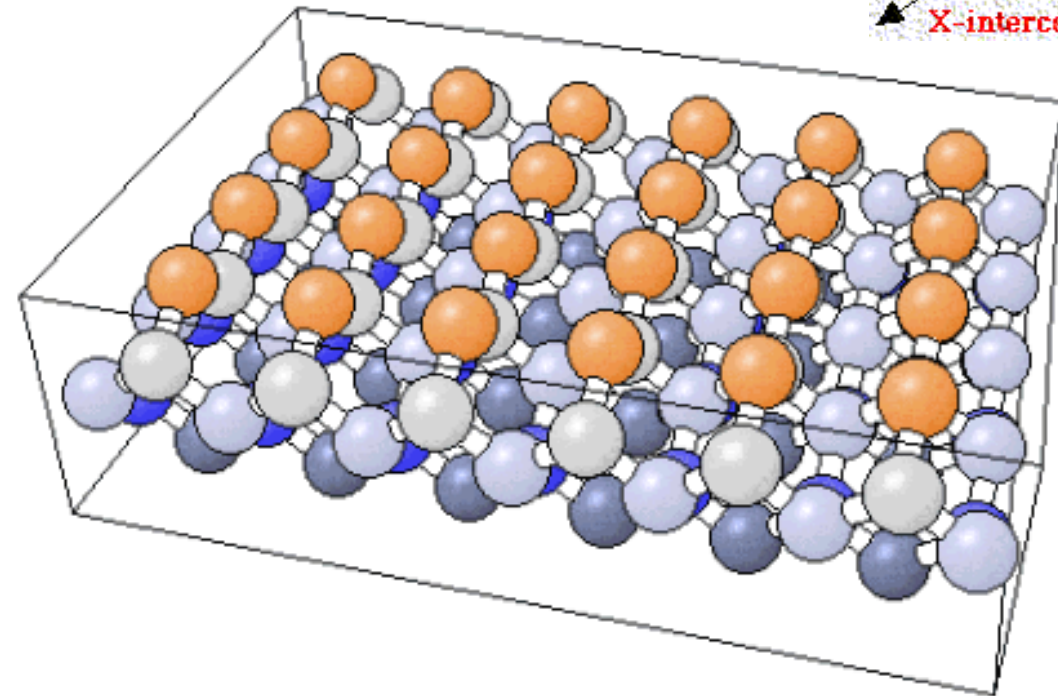
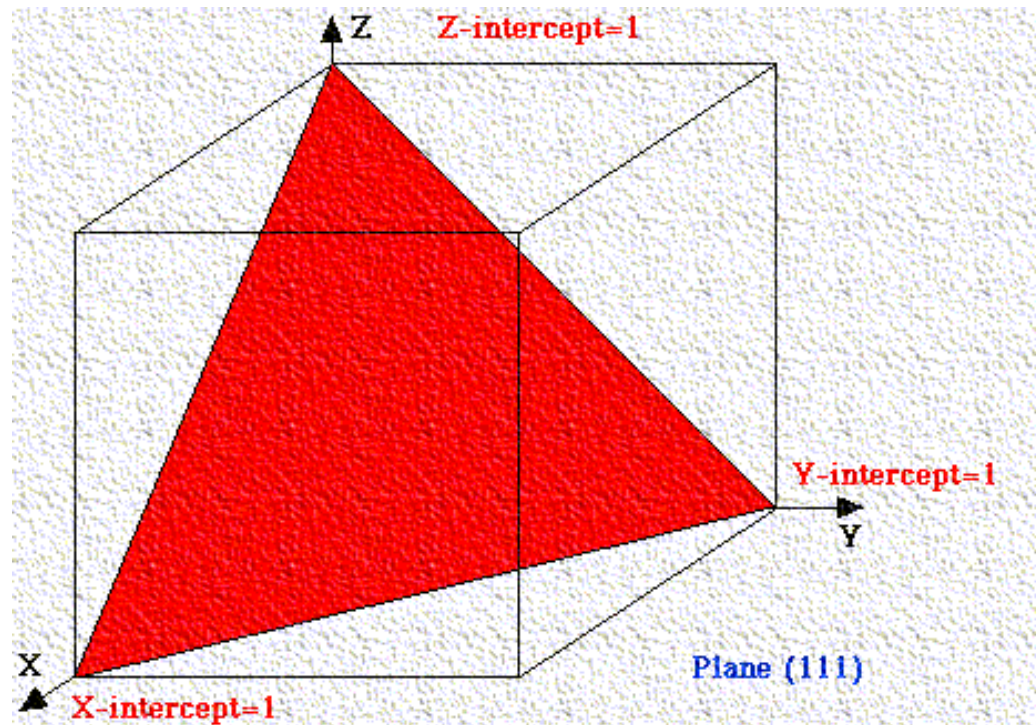


(011)

identical properties
in cubic lattice:
100 = 010 = 001

electronic properties
depend on crystal plane

Si (111) plane



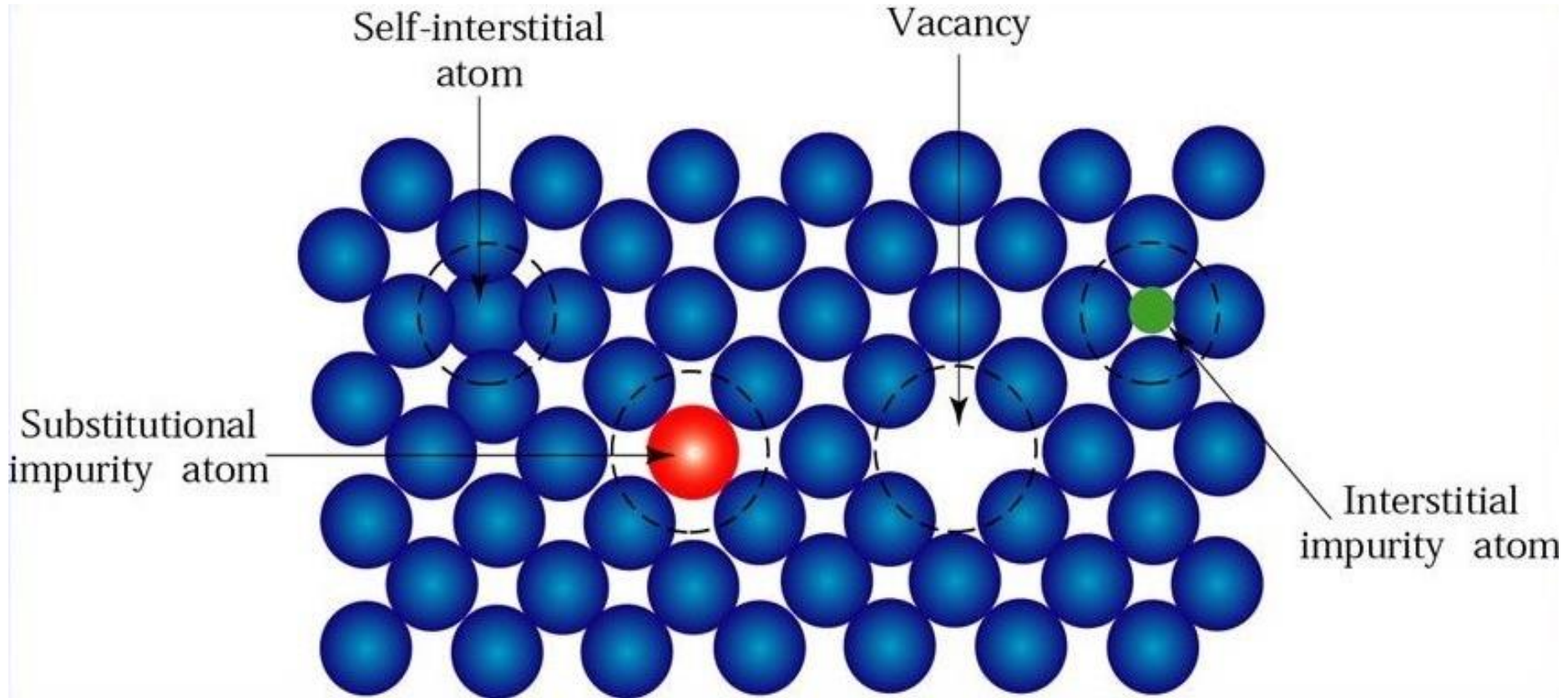
(100) has lesser atom density

- lesser current density
- lesser transistor capacity
- lesser crystal growth rate
- lesser oxidation rate

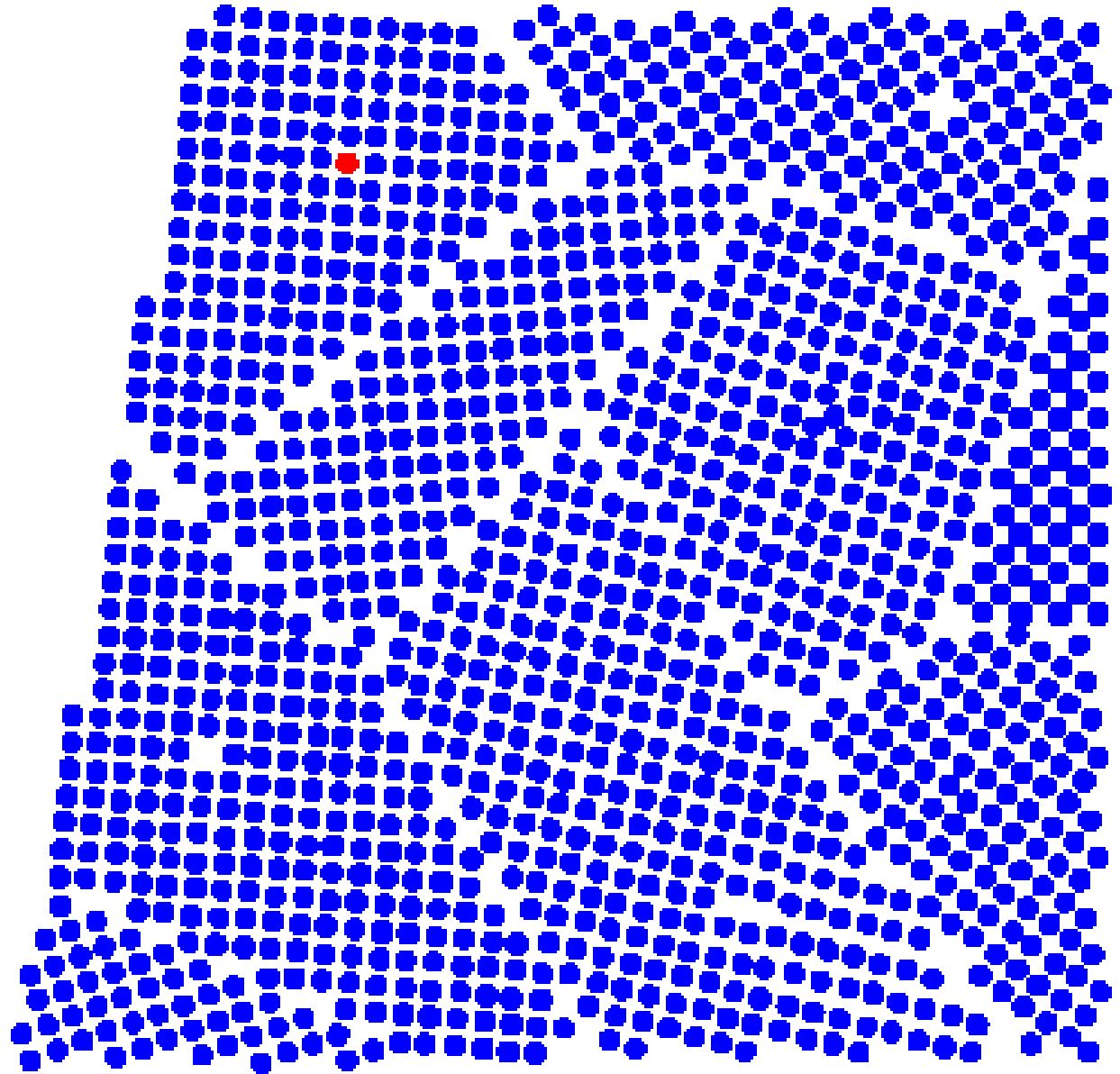
(100) is used for MOS FET

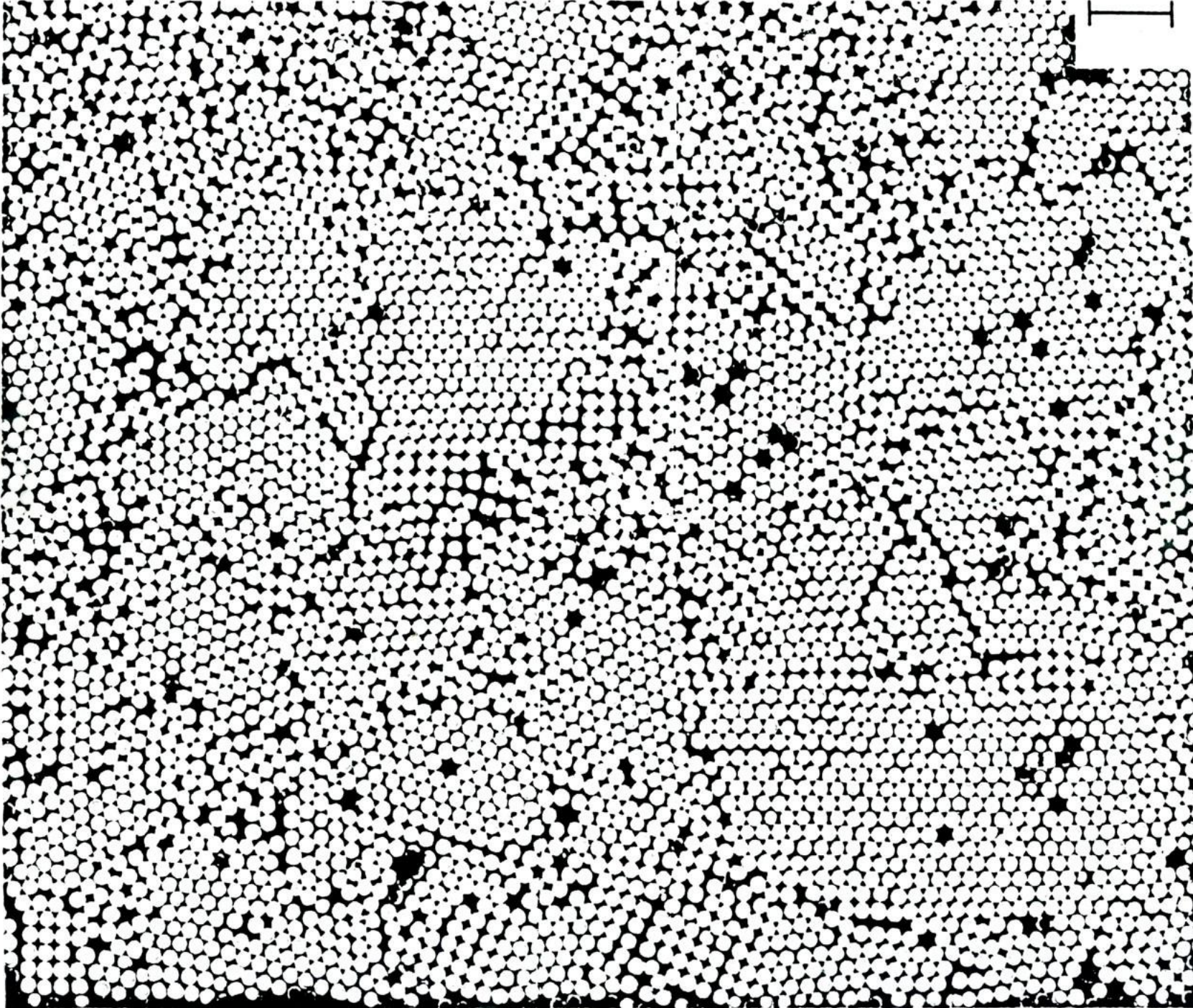
(111) hi power bipolar transistors

point defects

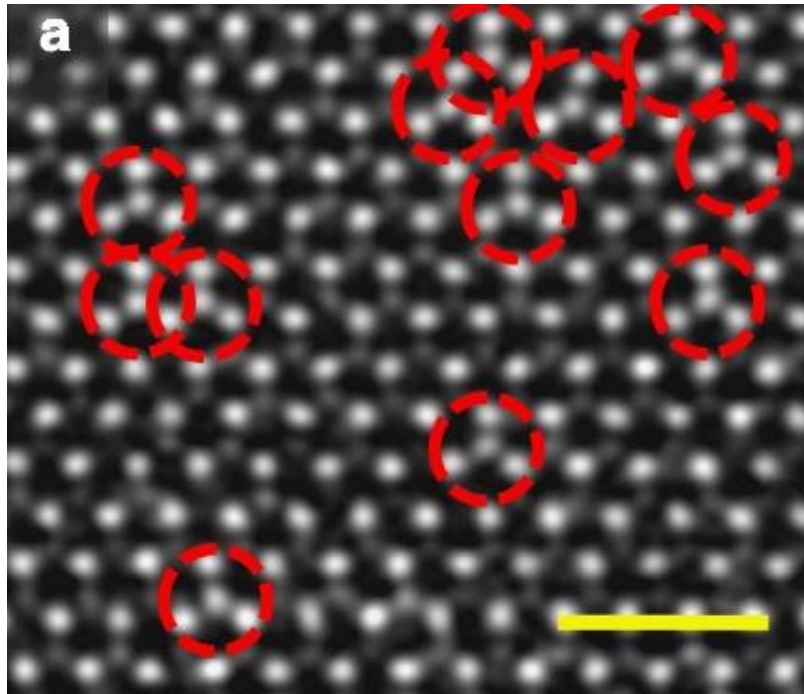


defects +
crystallites





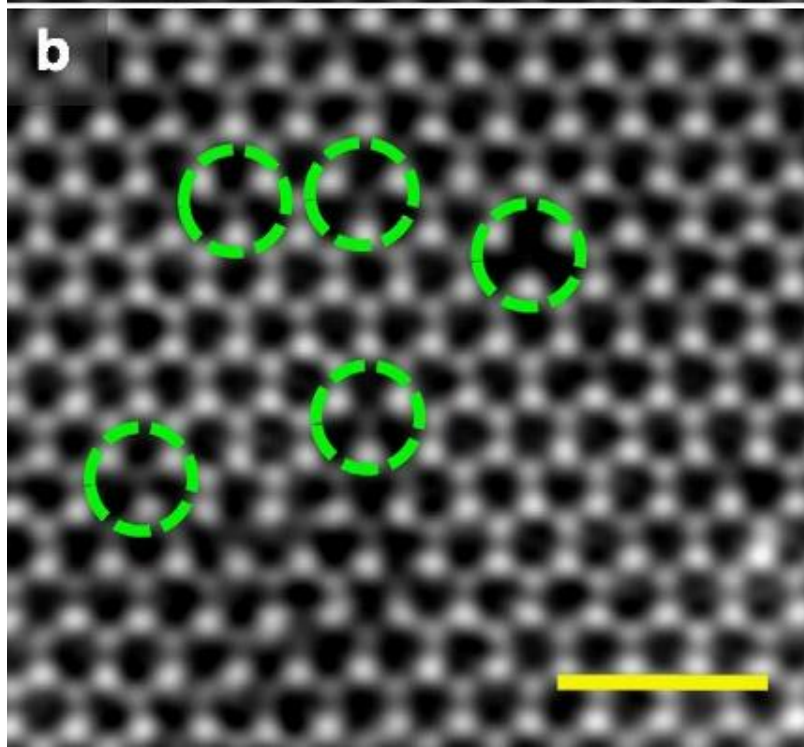
SEM



TEM

MoS₂ monolayer

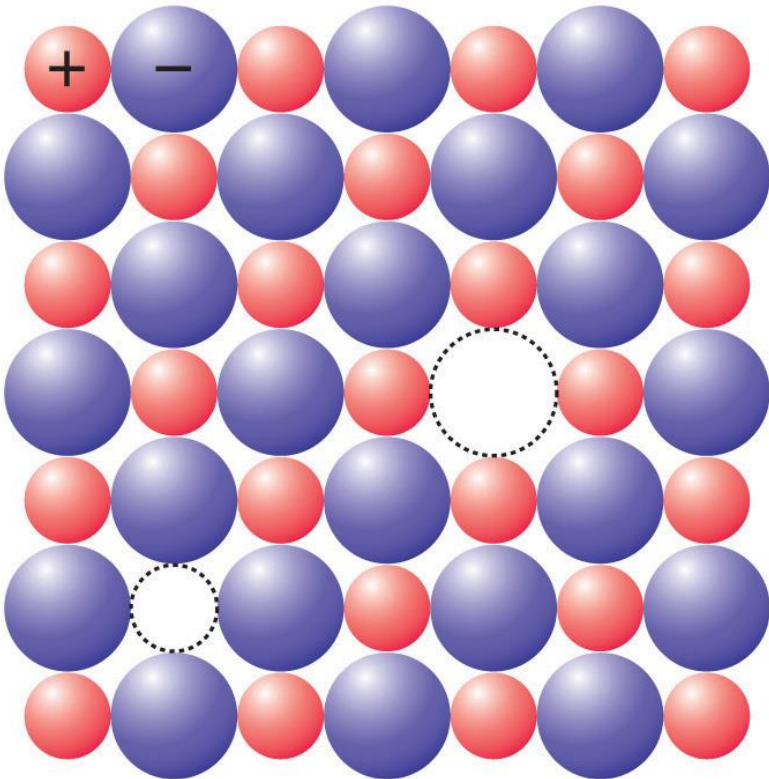
Mo substituted by S



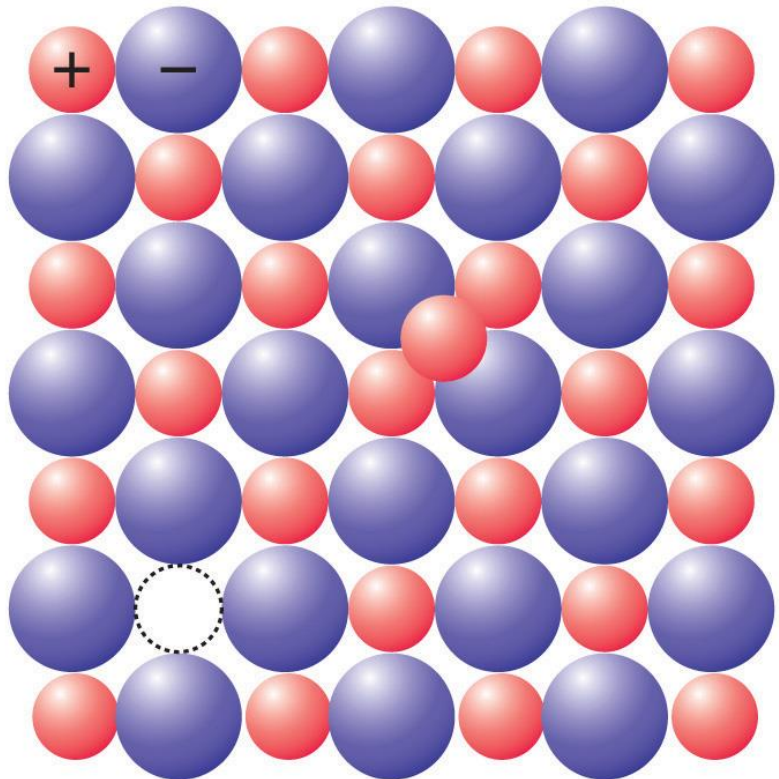
lack of S

scale 1 nm

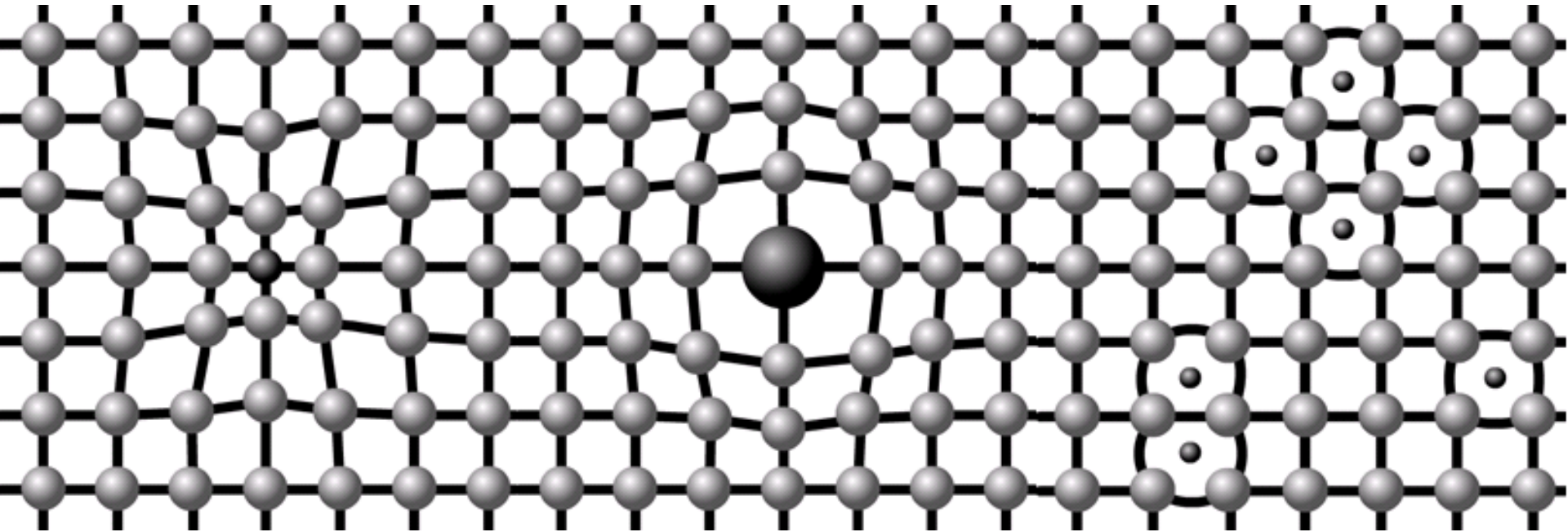
paired defects



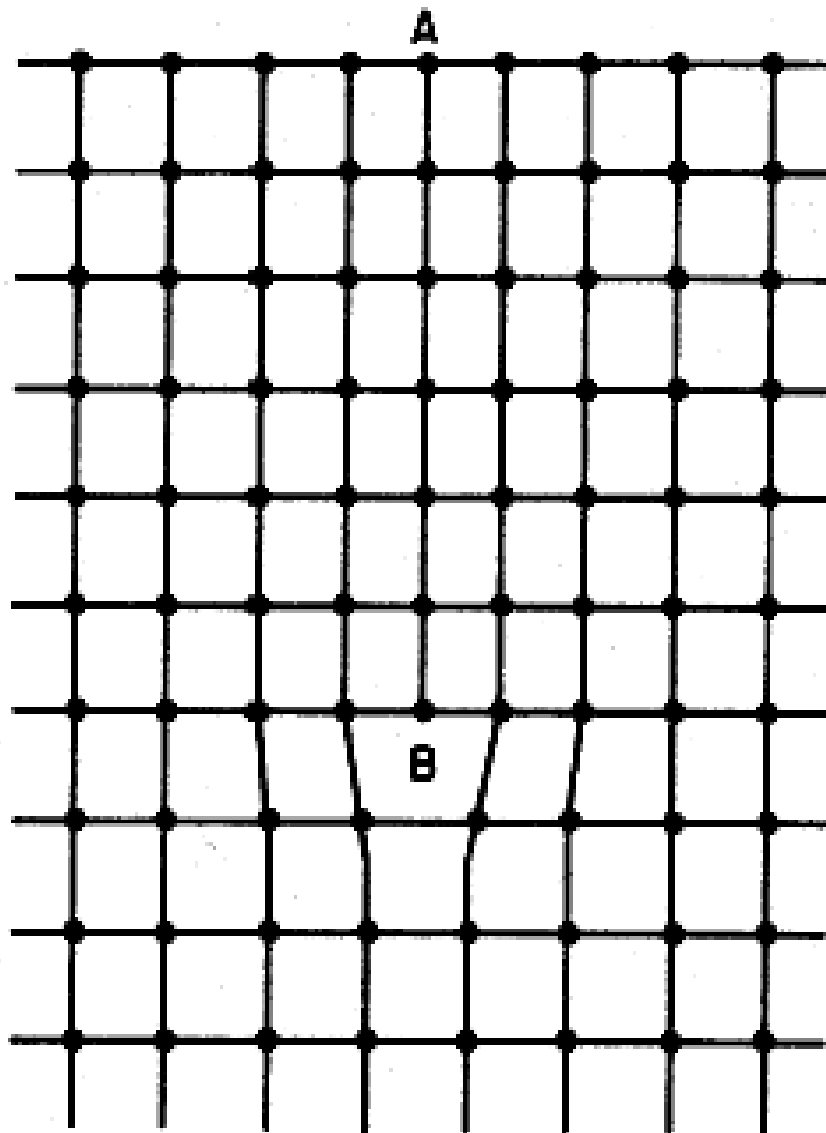
(a) Schottky defect



(b) Frenkel defect

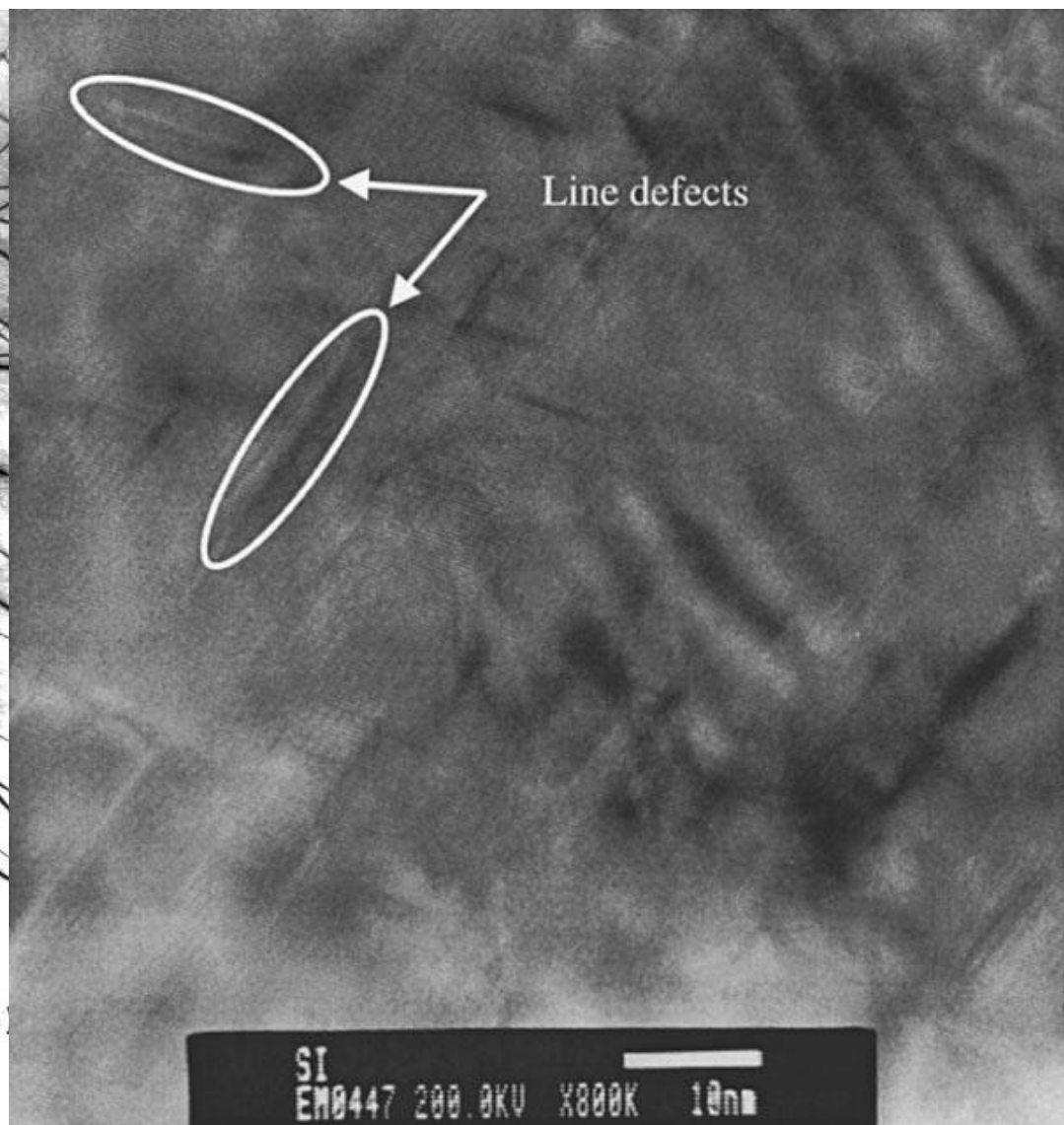
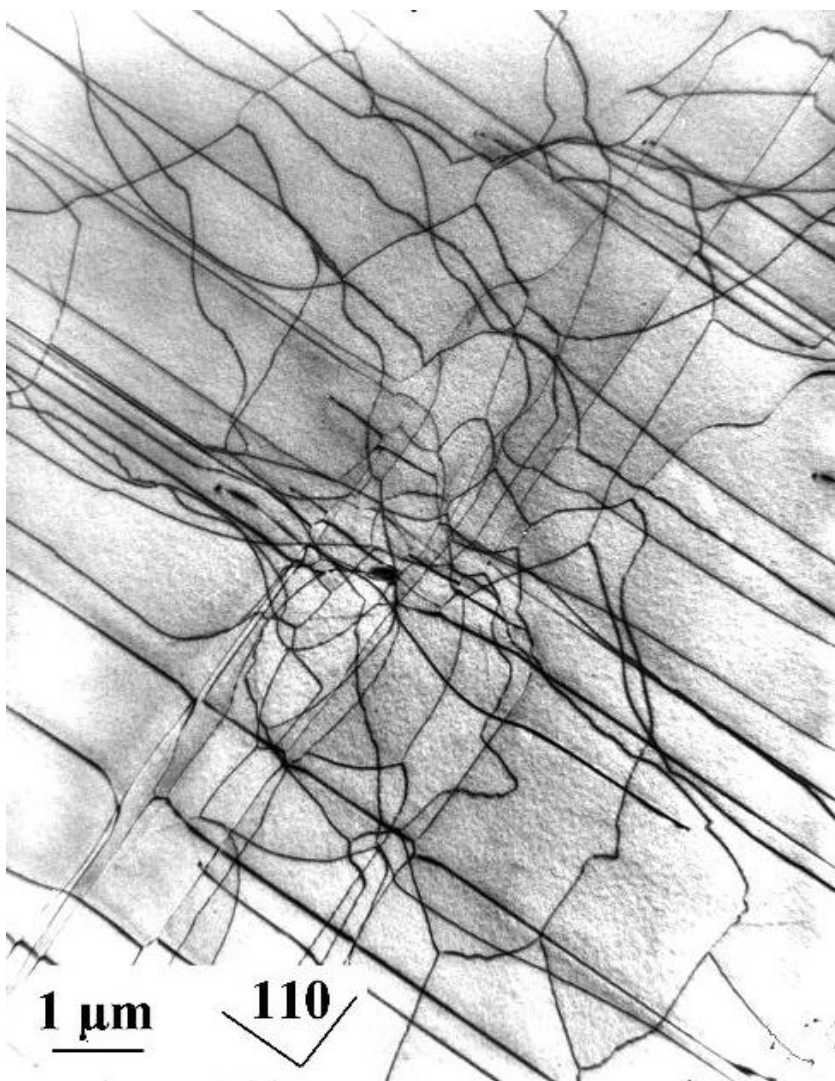


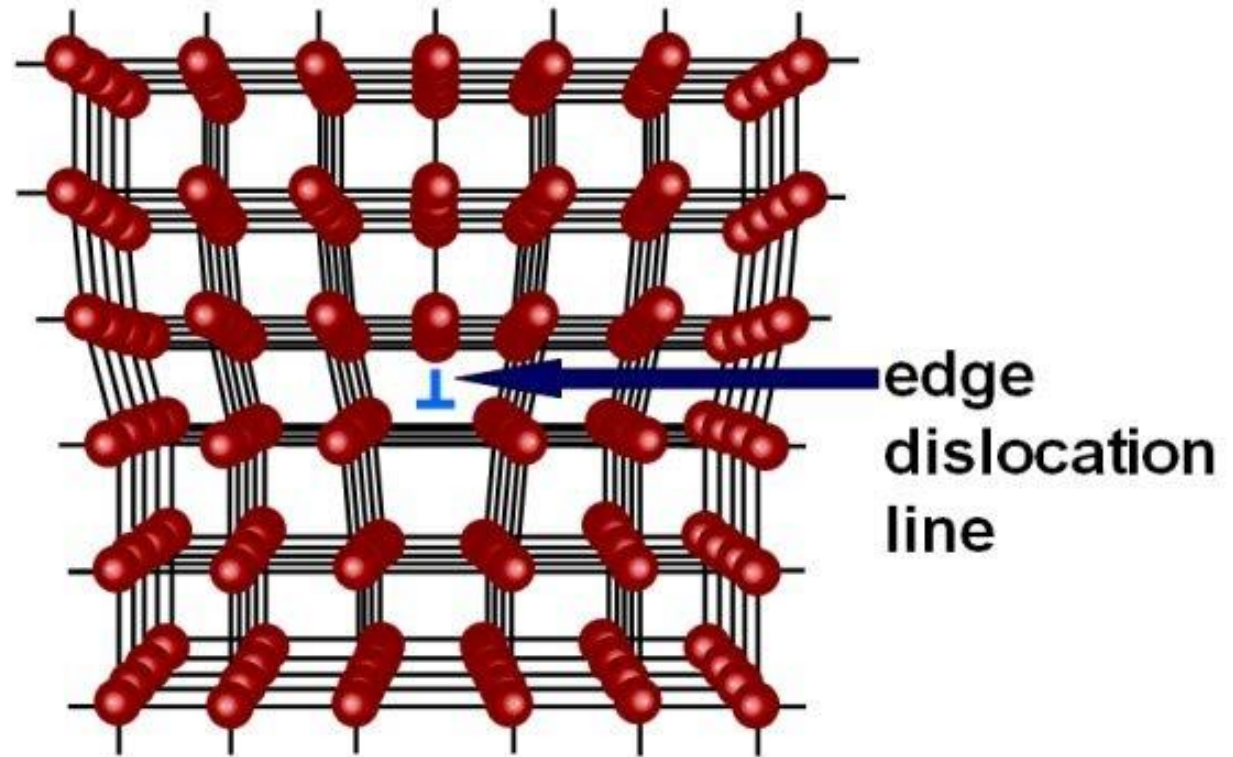
crystal defects result in **distortion of crystal lattice**



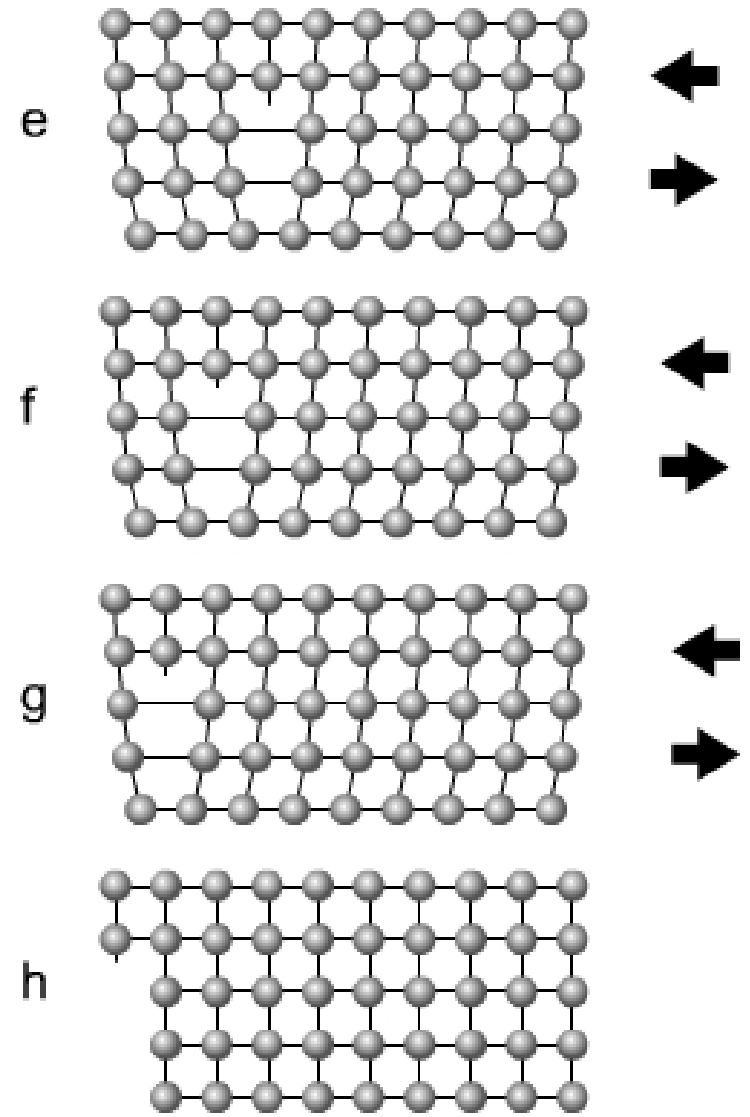
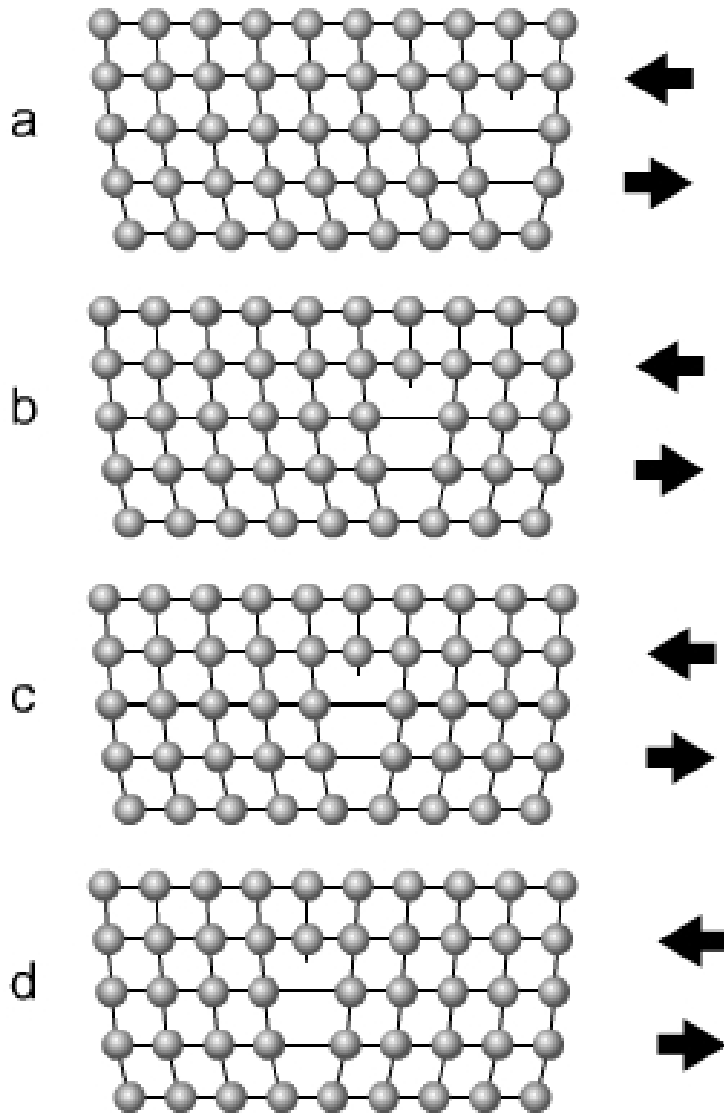
dislocation = linear defect

TEM
Si surface



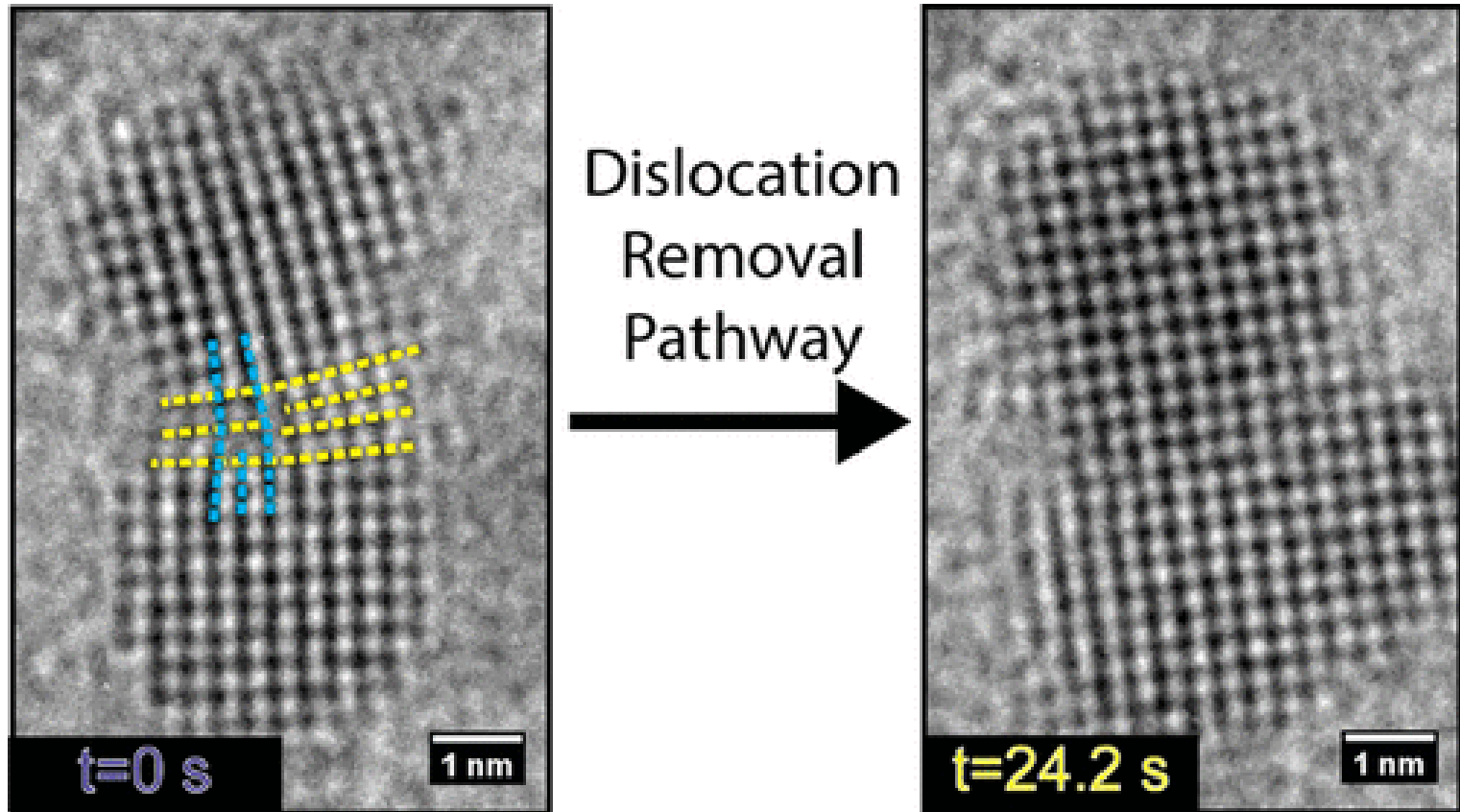


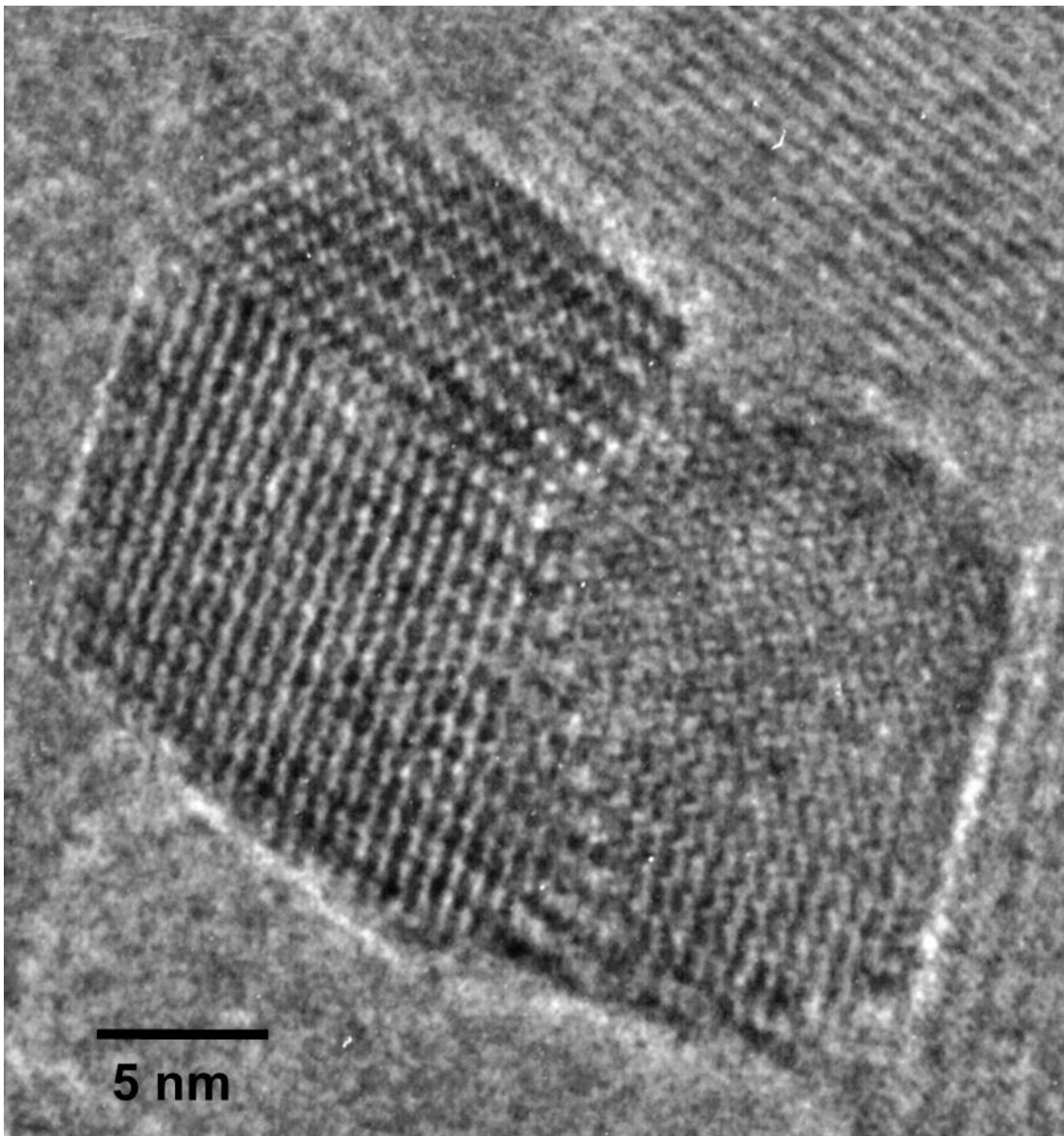
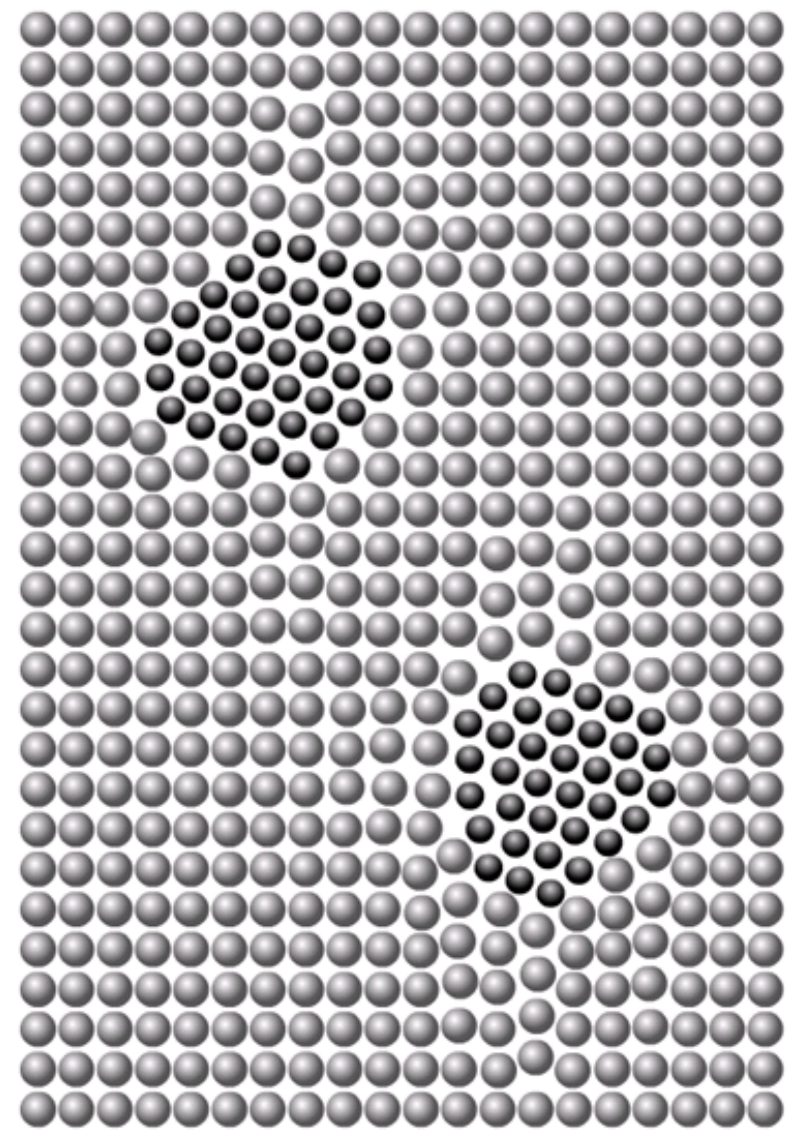
connected dislocations = **planar defects**



dislocations move in a crystal (at increased temperature)

PbTe crystal





defect clustering above solubility threshold